



### SIHG22N65E-GE3 Information



For Reference Only

**Part Number** SIHG22N65E-GE3 **Manufacturer** Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 650V 22A TO-247AC

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **Certified Quality**

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









# SIHG22N65E-GE3 Specifications

Manufacturer Part Number         SIHG22N65E-GE3           Manufacturer         Vishay Siliconix           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-247-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         650V           Current - Continuous Drain (Id) @ 25°C         22A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         110nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         2415pF @ 100V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         227W (Tc)           Rds On (Max) @ Id, Vgs         180 mOhm @ 11A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-247AC           Package / Case         TO-247-3		
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Package / Case TO-247-3	Mounting Type	Through Hole
	Supplier Device Package	TO-247AC
Report errors?	Package / Case	TO-247-3
		Report errors?

#### SIHG22N65E-GE3 Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## **SIHG22N65E-GE3 Payment Methods**





















### SIHG22N65E-GE3 Shipping Methods













If you have any question about SIHG22N65E-GE3, please do not hesitate to contact us!

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